Taiwan Semiconductor

N-Channel Power MOSFET

30V, 52A, 8.5mΩ

FEATURES

- Low R_{DS(ON)} to minimize conductive Losses
- Low gate charge for fast power switching
- 100% UIS and R_g tested
- Compliant to RoHS Directive 2011/65/EU and in accordance to WEEE 2002/96/EC
- Halogen-free according to IEC 61249-2-21 definition

PRODUCT SUMMARY				
PARAMETER		VALUE	UNIT	
V_{DS}		30	V	
R _{DS(on)} (max)	$V_{GS} = 10V$	8.5	0	
	$V_{GS} = 4.5V$	13	mΩ	
Q_g		7.2	nC	

Pb



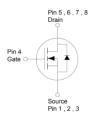


APPLICATIONS

- DC-DC Converters
- Battery Power Management
- ORing FET/Load Switch

PDFN33





Notes: MSL 1 (Moisture Sensitivity Level) per J-STD-020

ABSOLUTE MAXIMUM RATINGS (T _A = 25°C unless otherwise noted)				
PARAMETER		SYMBOL	LIMIT	UNIT
Drain-Source Voltage		V_{DS}	30	V
Gate-Source Voltage		V_{GS}	±20	V
Continuous Drain Current (Note 1)	$T_C = 25^{\circ}C$	l _D	52	
Continuous Drain Current	$T_A = 25$ °C		13	А
Pulsed Drain Current (Note 1)		I _{DM}	208	А
Single Pulse Avalanche Current (Note 2)		I _{AS}	23	А
Single Pulse Avalanche Energy (Note 2)		E _{AS}	26	mJ
Total Dower Discinstion	$T_C = 25^{\circ}C$	D	37	W
Total Power Dissipation	T _C = 125°C	P_{D}	7	VV
Total Power Dissipation	$T_A = 25^{\circ}C$	D	2.3	W
Total Power Dissipation	$T_A = 125^{\circ}C$	P_{D}	0.5	VV
Operating Junction and Storage Temperature Range		T_J,T_STG	- 55 to +150	°C

THERMAL RESISTANCE				
PARAMETER	SYMBOL	LIMIT	UNIT	
Thermal Resistance – Junction to Case	R _{eJC}	3.4	°C/W	
Thermal Resistance – Junction to Ambient	$R_{\Theta JA}$	53	°C/W	

Thermal Performance Note: $R_{\Theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistances. The case-thermal reference is defined at the solder mounting surface of the drain pins. $R_{\Theta JA}$ is guaranteed by design while $R_{\Theta CA}$ is determined by the user's board design.

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ELECTRICAL CHARACTERISTICS (T _A = 25°C unless otherwise noted)						
PARAMETER	CONDITIONS	SYMBOL	MIN.	TYP.	MAX.	UNIT
Static						
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250\mu A$	BV _{DSS}	30			V
Gate Threshold Voltage	$V_{GS} = V_{DS}, I_{D} = 250 \mu A$	$V_{GS(TH)}$	1	1.6	2.5	V
Gate-Source Leakage Current	$V_{GS} = \pm 20 V, V_{DS} = 0 V$	I _{GSS}			±100	nA
Drain-Source Leakage Current	$V_{GS} = 0V$, $V_{DS} = 30V$	I _{DSS}			1	μA
Drain-Source On-State Resistance	$V_{GS} = 10V, I_D = 13A$	_		6.2	8.5	mΩ
(Note 3)	$V_{GS} = 4.5V, I_D = 13A$	$R_{DS(on)}$		9	13	
Forward Transconductance (Note 3)	$V_{DS} = 5V, I_{D} = 13A$	g _{fs}		27		S
Dynamic (Note 4)						
Total Gate Charge	$V_{GS} = 10V, V_{DS} = 15V,$ $I_{D} = 13A$	Q_g		14.3		
Total Gate Charge		Q_g		7.2		nC
Gate-Source Charge	$V_{GS} = 4.5V, V_{DS} = 15V,$	Q_gs		2.6		
Gate-Drain Charge	I _D = 13A	Q_gd		3.4		
Input Capacitance		C _{iss}		817		
Output Capacitance	$V_{GS} = 0V, V_{DS} = 15V,$ f = 1.0MHz	C _{oss}		155		pF
Reverse Transfer Capacitance	1 = 1.0001112	C _{rss}		96		
Gate Resistance	f = 1.0MHz, open drain	R_g	0.8	2.8	5.6	Ω
Switching (Note 4)						
Turn-On Delay Time		t _{d(on)}		4.8		
Rise Time	$V_{GS} = 10V, V_{DS} = 15V,$ $I_D = 15A, R_G = 3.3\Omega,$	t _r		12.5		
Turn-Off Delay Time		t _{d(off)}		27.6		ns
Fall Time		t _f		8.2		
Source-Drain Diode						
Diode Forward Voltage (Note 3)	$V_{GS} = 0V, I_{S} = 13A$	V _{SD}			1	V
Reverse Recovery Time	I _S = 13A,	t _{rr}		13		ns
Reverse Recovery Charge	di/dt = 100A/µs	Q _{rr}		6.3		nC

Notes:

- 1. Current limited by package.
- 2. $L=0.1mH,\ V_{GS}=10V,\ V_{DS}=25V,\ R_G=25\Omega,\ I_{AS}=23A,\ Starting\ T_J=25^{\circ}C$
- 3. Pulse test: Pulse Width \leq 300 μ s, duty cycle \leq 2%.
- 4. Switching time is essentially independent of operating temperature.

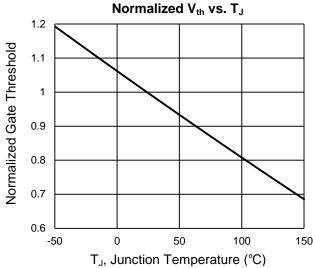
ORDERING INFORMATION

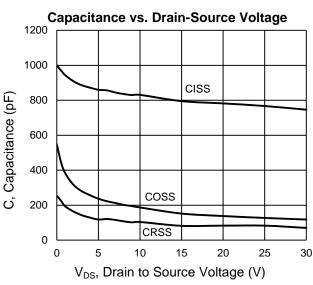
PART NO.	PACKAGE	PACKING
TSM085N03PQ33 RGG	PDFN33	5,000pcs / 13" Reel

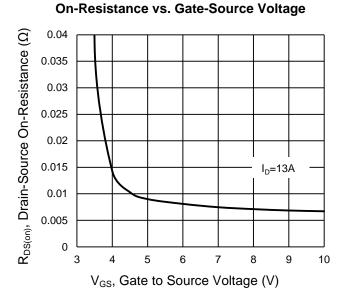


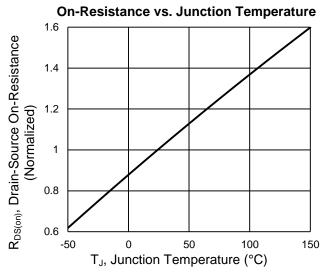
CHARACTERISTICS CURVES

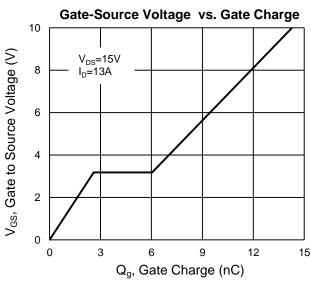
 $(T_A = 25^{\circ}C \text{ unless otherwise noted})$



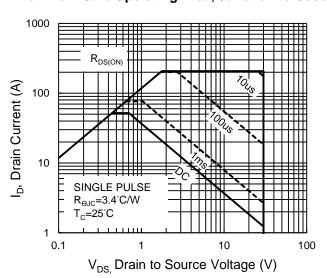








Maximum Safe Operating Area, Junction-to-Case



Version: D1608

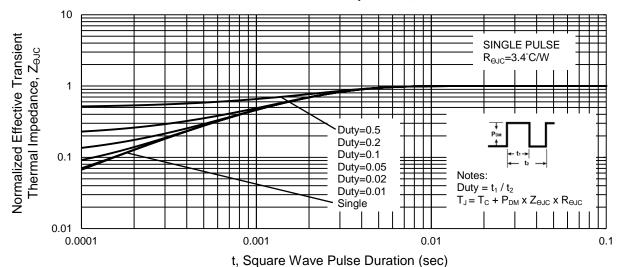
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CHARACTERISTICS CURVES

(T_A = 25°C unless otherwise noted)

Normalized Thermal Transient Impedance, Junction-to-Case



Version: D1608

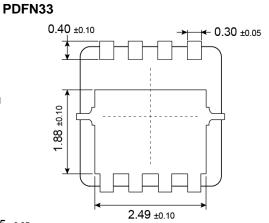
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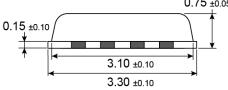


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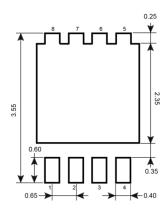
PACKAGE OUTLINE DIMENSIONS (Unit: Millimeters)

3.10 ±0.10 3.35 ± 0.10 0.65 (REF) 0.75 ±0.05





SUGGESTED PAD LAYOUT (Unit: Millimeters)



MARKING DIAGRAM



Y = Year Code

M = Month Code for Halogen Free Product

O =Jan P =Feb Q =Mar R =Apr

S = May T = Jun

V =Aug

W =Sep X =Oct

U =Jul

Y =Nov Z =Dec

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L = Lot Code (1~9, A~Z)



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